Product data sheet

1. Product profile

1.1 General description

Ultrafast, epitaxial rectifier diode in a SOD59 (TO-220AC) plastic package.

1.2 Features

- Fast switching
- Soft recovery characteristic
- Low forward voltage drop
- Low thermal resistance
- High thermal cycling performance

1.3 Applications

- High frequency switched-mode power supplies
- Discontinuous Current Mode (DCM)Power Factor Correction (PFC)

1.4 Quick reference data

- V_{RRM} ≤ 600 V
- V_F ≤ 1.11 V

- $I_{F(AV)} \le 9 A$
- $t_{rr} \le 60 \text{ ns}$

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	cathode (k)		
2	anode (a)	mb	k — ← a <i>001aaa020</i>
mb	mounting base; cathode	1 2	
		SOD59 (2-lead TO-220)	AC)



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3. Ordering information

Table 2. Ordering information

Type number	Package					
	Name	Description	Version			
BYV29-600	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59			

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

	<u> </u>	<u> </u>			
Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	square waveform; δ = 1.0; $T_{mb} \le 100$ °C	-	600	V
I _{F(AV)}	average forward current	square waveform; δ = 0.5; $T_{mb} \leq$ 120 $^{\circ}C$	-	9	Α
I _{FRM}	repetitive peak forward current	square waveform; δ = 0.5; $T_{mb} \leq$ 120 $^{\circ}C$	-	18	Α
I _{FSM}	non-repetitive peak forward current	t = 10 ms; sinusoidal waveform	-	70	Α
		t = 8.3 ms; sinusoidal waveform	-	77	Α
T _{stg}	storage temperature		-40	+150	°C
Tj	junction temperature		-	150	°C

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; see Figure 1	-	-	2.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

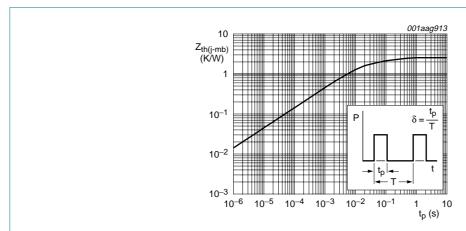


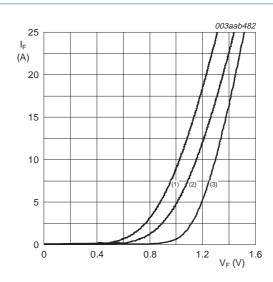
Fig 1. Transient thermal impedance from junction to mounting base as a function of pulse width

6. Characteristics

Table 5. Characteristics

 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

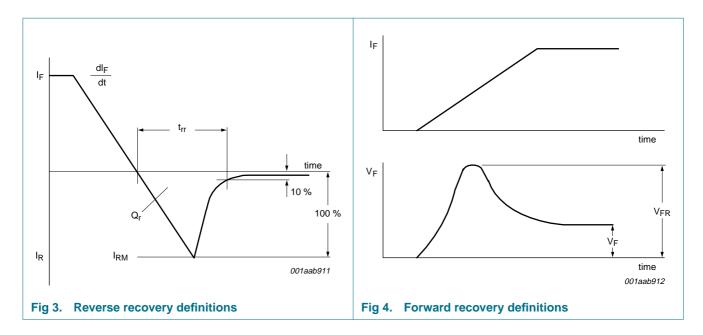
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _F	forward voltage	$I_F = 8 \text{ A}$; $T_j = 150 ^{\circ}\text{C}$; see Figure 2	-	0.97	1.11	V
		I _F = 8 A	-	1.12	1.25	V
		I _F = 20 A; see Figure 2	-	1.31	1.45	V
I _R	reverse current	V _R = 600 V	-	2	50	μΑ
		$V_R = 600 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	0.1	0.35	mA
Dynamic o	characteristics					
Q _r	recovered charge	I_F = 2 A to V_R \geq 30 V; dI_F/dt = 20 A/ μ s; see Figure 3	-	40	70	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A to V}_R \ge 30 \text{ V};$ $dI_F/dt = 100 \text{ A/}\mu\text{s}; \text{ see } \frac{\text{Figure 3}}{}$	-	50	60	ns
I _{RM}	peak reverse recovery current	I_F = 10 A to V_R \geq 30 V; dI_F/dt = 50 A/ μ s; T_j = 100 °C; see Figure 3	-	3	5.5	Α
V_{FR}	forward recovery voltage	$I_F = 10 \text{ A}$; $dI_F/dt = 10 \text{ A/}\mu\text{s}$; see Figure 4	-	3.2	-	V



- (1) $T_j = 150 \,^{\circ}\text{C}$; typical values
- (2) T_i = 150 °C; maximum values
- (3) $T_j = 25$ °C; maximum values

Fig 2. Forward current as a function of forward voltage

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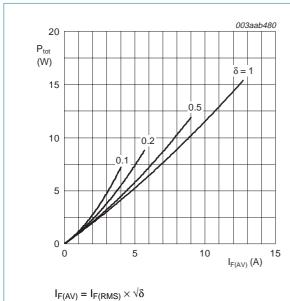


Fig 5. Forward power dissipation as a function of average forward current; square waveform; maximum values

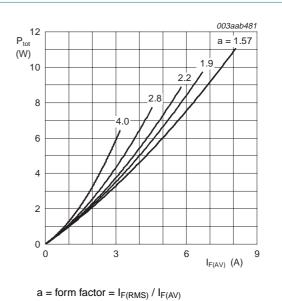


Fig 6. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC

SOD59

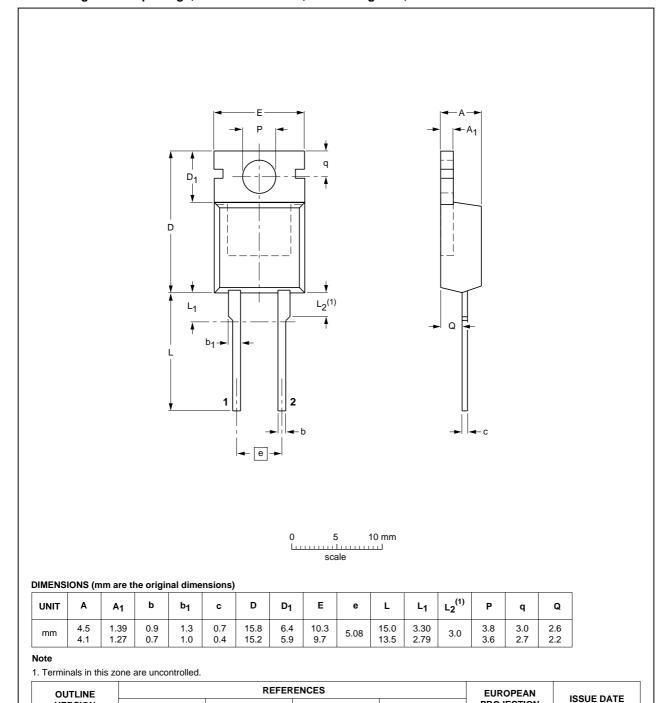


Fig 7. Package outline SOD59 (2-lead TO-220AC)

IEC

JEDEC

2-lead TO-220AC

VERSION

SOD59

JEITA

99-09-13

PROJECTION

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8. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV29-600_2	20071024	Product data sheet	-	BYV29-600_1
Modifications: • The format of this data sheet has been redesigned to comply with the new identity guid NXP Semiconductors.				new identity guidelines of
	 Legal texts have 	ave been adapted to the new o	company name where appre	opriate.
	• Table 5 "Chai	racteristics" on page 3: V _F valu	ues updated.	
BYV29-600_1	20000201	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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